

Espacenet

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NANOSIZE VERTICAL TRANSISTOR USING CARBON NANOTUBE AND METHOD OF MANUFACTURING THE TRANSISTOR

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Abstract of JP 2802110977 (A)

PROBLEM TO BE SOLVED: To provide a regionize vertical transferor using carbon haridables which can be integrated at a high degree of integration as a tere-bit scale, and to provide a method of mane/populing the translator, SQLUTION; Holes, 107, having diameters of several hm, are made through an insularing film 10 of alumina, moultomed on a substrate and parbon nanoubes 100 are formed by at least one method selected from a chemical vapor phase tilm torning method, an electrophoresis method, and a mechanical method and enranged vertically in the hotes 10' as channels.. In addition, gate stectrodes 20 are formed near the peripheries of the nanotings 100, by using the conventional semiconductor device manufacturing method and, at the same time, thin recommonductor films, 30 are formed on the gate electrodes 20 so as to bury the holes: 10' and source electrodes 40 and drain electrodes 50 are cospectively formed on and under the pancitubes 100, Consequently, the narrosize vertical transistor, which has a vertical structure of a terra-bit scale, operates with little power consumption, and uses the carbon nanofubes 100, is obtained.

